

100V N-Channel Power MOSFET

Pb RoHS

TO-252 (DPAK)



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
100	13 @ V _{GS} =10V	70

Features

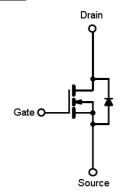
- Advanced Trench Technology
- Low $R_{DS(ON)} 13m\Omega$ (Max.)
- Low gate charge typical @ 145nC (Typ.)
- Low Crss typical @ 120pF (Typ.)

Ordering Information

Part No.	Package	Packing		
TSM70N10CP ROG	TO-252	2.5Kpcs / 13" Reel		

Note: "G" denote for Halogen Free Product

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	±20	V	
	T _C =25℃		70		
Continuous Drain Current	T _C =70℃		61	Α	
Continuous Drain Current	T _A =25℃	l _D	12		
	T _A =70℃		9		
Drain Current-Pulsed Note 1		I _{DM}	150	Α	
Avalanche Current, L=0.5mH		I _{AS} , I _{AR}	25	А	
Avalanche Energy, L=0.5mH		E _{AS} , E _{AR}	156	mJ	
	T _C =25℃		120		
Maximum Dowar Dissipation	T _C =70℃	P_{D}	80	W	
Maximum Power Dissipation	T _A =25℃	P _D	8.3		
	T _A =70℃		5.3		
Storage Temperature Range		T _{STG}	-55 to +150	${\mathfrak C}$	
Operating Junction Temperature Range		T _J	-55 to +150	C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	1	°C/W	
Thermal Resistance - Junction to Ambient	R⊖ _{JA}	40	°C/W	

Notes: Surface mounted on FR4 board t ≤ 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}	1	10	13	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I _{DSS}	1		1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 50V, I_{D} = 30A,$ $V_{GS} = 10V$	Q_g	1	145		nC
Gate-Source Charge		Q_{gs}	1	25		
Gate-Drain Charge		Q_{gd}		43		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{iss}		4300		
Output Capacitance		C _{oss}		300		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}	1	120		
Switching						
Turn-On Delay Time		t _{d(on)}		27		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 50V,$	t _r		13		~0
Turn-Off Delay Time	$R_G = 3\Omega$	$t_{d(off)}$		15		nS
Turn-Off Fall Time		t _f		42		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	V _{SD}		0.8	1.3	V
Reverse Recovery Time	$I_S = 30A$, $T_J = 25$ °C dI/dt = 100A/us	t _{fr}		165		nS
Reverse Recovery Charge		Q _{fr}		175		nC

Notes

^{1.} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

^{2.} $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

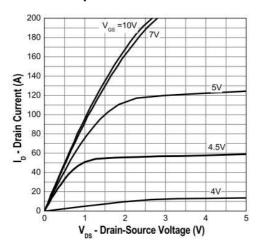


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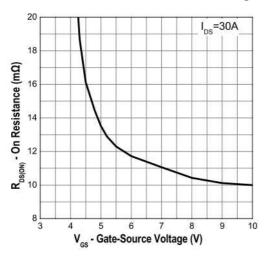


Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

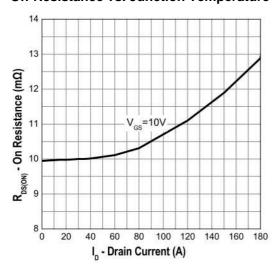
Output Characteristics



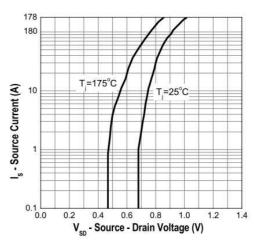
On-Resistance vs. Gate-Source Voltage



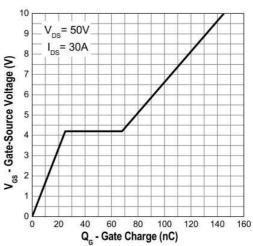
On-Resistance vs. Junction Temperature



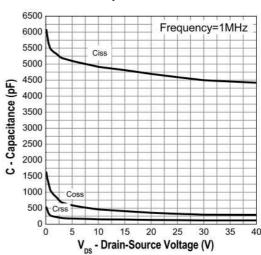
Transfer Characteristics



Gate Charge



Capacitance

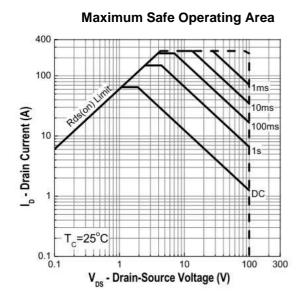




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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



I_{DS} =250uA 1.2 Normalized Threshold Voltage 0.9 0.8 0.6

50 75

T. - Junction Temperature (°C)

125

150 175

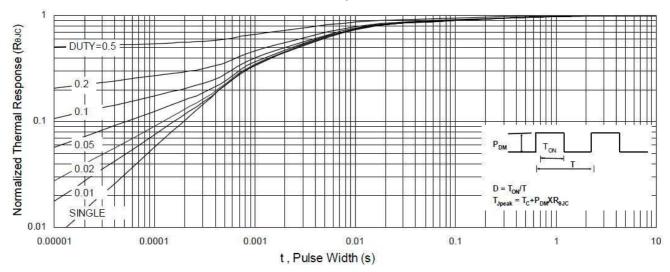
Threshold Voltage vs. Temperature

Normalized Thermal Transient Impedance, Junction-to-Ambient

0.5

0.4 -50

-25



4/6

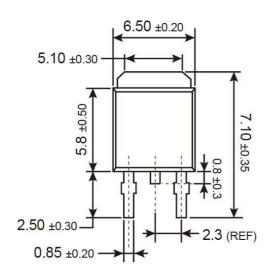
Version: B13

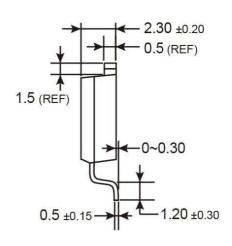


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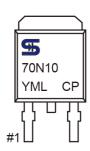
TO-252 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code



TSM70N10 100V N-Channel Power MOSFET

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